

Features

- 2K x 8 bit CMOS static RAM with 3-state outputs
- Dual-port with on-chip arbitration logic
- High speed
 - Maximum access time of 55/70/90/120 ns
- Battery backup 2 volt data retention
- Low power operation
 - operating 325 mW (typ)
 - standby 15 μ W (typ)
- VICMOS process virtually eliminates alpha particle induced soft errors
- Full CMOS memory cell
- Both ports fully asynchronous
- Single 5 volt power supply
- TTL compatible

Description

The Vitelic V61C32 is a CMOS 2K x 8 high-speed dual port static RAM with advanced arbitration logic to provide 55 ns access to both ports simultaneously. Fabrication with VICMOS technology provides a high-performance, low-power alternative to NMOS memory.

The Vitelic V61C32 provides two parallel 8-bit ports with separate controls, addresses, and I/O permitting read or write access to any memory location. Automatic power-down circuitry permits a port to be placed in the standby mode when $\overline{CE}$ is high.

The $\overline{BUSY}$ signal is used to indicate an attempt by both ports to access simultaneously to the same address location. The signal may be ignored or acted upon as required by system design. If both ports are attempting to read or write the same address location simultaneously, data can be compromised and $\overline{BUSY}$ will be asserted on the port denied access.

The Vitelic V61C32 offers a battery backup data retention mode where the device typically consumes only 2.5 μ W from a 2 volt source.

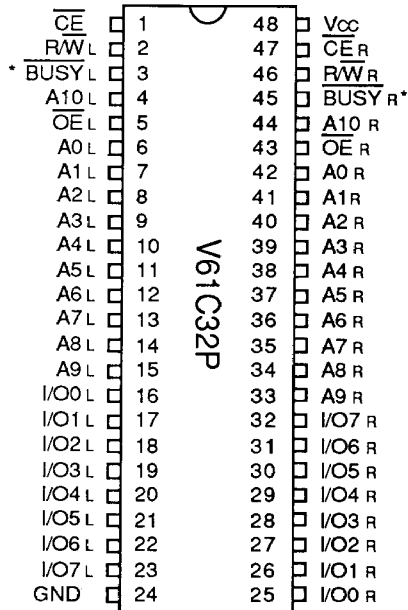
Device Usage Chart

Operating Temperature Range	Package Outline				Access Time (ns)				Power		Temperature Mark
	P	J	AJ		55	70	90	120	Low	Std.	
0°C to 70°C	•	•	•		•	•	•		•	•	Blank
-40°C to +85°C	•	•	•			•	•	•	•	•	I

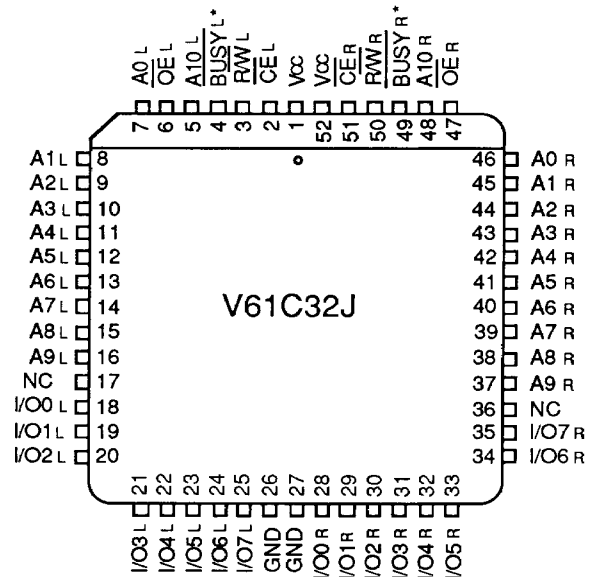
Package	Std.	Pin Count
Plastic DIP	P	48
PLCC (J Lead)	J	52
PLCC (J Lead)	AJ	52

V	C			T		T	T
Family	Device	Package	Speed	Power	Temp		

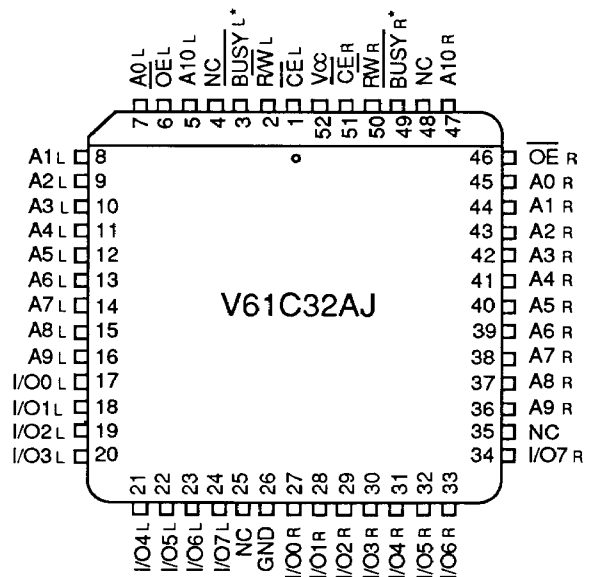
DIP
PIN CONFIGURATION
Top View



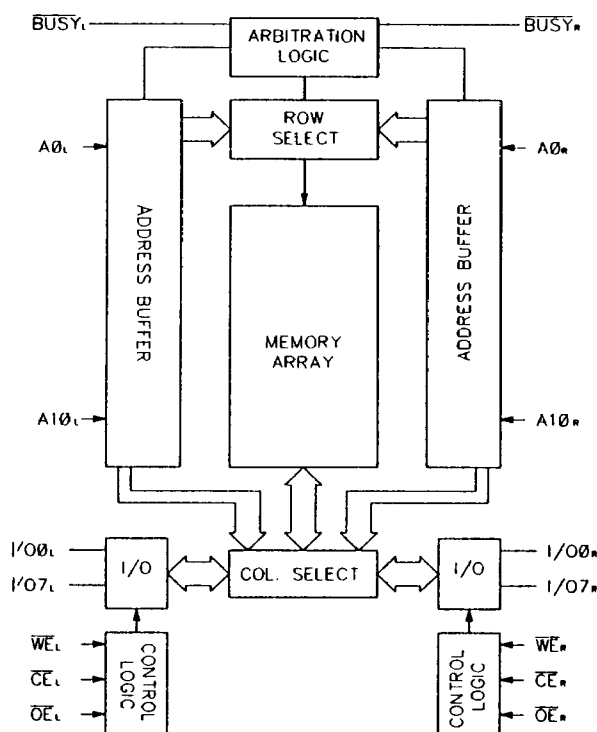
PLCC
PIN CONFIGURATION
Top View



PLCC
PIN CONFIGURATION
Top View



*NOTE: THE BUSY SIGNAL IS AN OPEN DRAIN OUTPUT, AND THUS REQUIRES A PULL-UP RESISTOR

BLOCK DIAGRAM

Absolute Maximum Ratings ⁽¹⁾

Symbol	Parameter	Rating	Unit
V _{TERM}	Voltage on any Pin with Respect to V _{SS}	-0.5* to +7.0	V
T _A	Operating Temperature Under Bias	Same as Recommended Operating Conditions	°C
T _{STG}	Storage Temperature	-65 to +150	°C
P _T	Power Dissipation	1.0	W
I _{OUT}	DC Output Current	50	mA

*-3.5V for 20 ns pulse.

NOTE:

1. Operation at or near absolute maximum ratings can affect device reliability.

Recommended Operating Conditions

T_A = Operating Temperature Range

Range	Temperature
Commercial	0°C to 70°C
Industrial	-40°C to +95°C
Extended	-55°C to +125°C

Symbol	Parameter	Min.	Typ.	Max.	Unit
V _{DD}	Supply Voltage	4.5	5.0	5.5	V
V _{SS}	Supply Voltage	0.0	0.0	0.0	V
V _{IH}	Input High Voltage	2.2	3.5	V _{DD}	V
V _{IL}	Input Low Voltage	-0.5*	—	+0.8	V

*-3.5V for 20 ns pulse.

Capacitance

T_A = 25°C, f = 1.0 MHz

Symbol	Parameter	Conditions	Max.	Unit
C _{OUT}	Output Capacitance	V _{IN} = 0V	5	pF
C _{IN}	Input Capacitance	V _{OUT} = 0V	5	pF

Non-Contention Read-Write Control

Left Port Inputs			Right Port Inputs			Flags		Function
R/W _L	CE _L	OE _L	R/W _R	CE _R	OE _R	BUSY _L	BUSY _R	
X	H	X	X	X	X	H	H	Left Port in Power Down Mode
X	X	X	X	H	X	H	H	Right Port in Power Down
L	L	X	X	X	X	H	H	Data on Left Port Written Into Memory
H	L	L	X	X	X	H	H	Data in Memory Output on Left Port
X	X	X	L	L	X	H	H	Data on Right Port Written Into Memory
X	X	X	H	L	L	H	H	Data in Memory Output on Right Port

H = High, L = Low, X = Don't Care

CE Arbitration with Address Match Before CE

Left Port				Right Port				Flags		Function
R/W _L	CE _L	OE _L	A _{0L} -A _{10L}	R/W _R	CE _R	OE _R	A _{0R} -A _{10R}	BUSY _L	BUSY _R	
X	LBR	X	Match	X	L	X	Match	H	L	Left Operation Permitted Right Operation Not Permitted
X	L	X	Match	X	LBL	X	Match	L	H	Left Operation Not Permitted Right Operation Permitted
X	LST	X	Match	X	LST	X	Match	H	L	Left Operation Permitted Right Operation Not Permitted

NOTE:

X = Don't Care, L = Low, H = High, LST = Low Same Time, LBR = Low Before Right, LBL = Low Before Left

Address Arbitration with CE Low Before Address Match

Left Port				Right Port				Flags		Function
R/W _L	CE _L	OE _L	A _{0L} -A _{10L}	R/W _R	CE _R	OE _R	A _{0R} -A _{10R}	BUSY _L	BUSY _R	
X	L	X	VBR	X	L	X	Valid	H	L	Left Operation Permitted Right Operation Not Permitted
X	L	X	Valid	X	L	X	VBL	L	H	Left Operation Not Permitted Right Operation Permitted
X	L	X	VST	X	L	X	VST	H	L	Left Operation Permitted Right Operation Not Permitted

NOTE:

X = Don't Care, L = Low, H = High, VST = Valid Same Time, VBR = Valid Before Right, VBL = Valid Before Left

DC Characteristics

For operating conditions, refer to Temperature Range Marking

Symbol	Parameter	Test Conditions	Range	V61C32			V61C32L			Unit
				Min.	Typ. ⁽¹⁾	Max.	Min.	Typ. ⁽¹⁾	Max.	
I_{LI}	Input Leakage Current	$V_{DD} = 5.5V, V_{IN} = 0.0V \text{ to } V_{DD}$	—	—	—	10	—	—	5	μA
			—	—	—	10	—	—	5	
			X	—	—	20	—	—	10	
I_{LO}	Output Leakage Current	$\overline{CE} \leq V_{IL}, V_{OUT} = 0.0V \text{ to } V_{DD}$	—	—	—	10	—	—	5	μA
			I	—	—	10	—	—	5	
			X	—	—	20	—	—	10	
V_{IH}	Input High Voltage			2.2	—	6.0	2.2	—	6.0	V
V_{IL}	Input Low Voltage			-0.5 ⁽²⁾	—	+0.8	-0.5 ⁽²⁾	—	+0.8	V
I_{DD}	Dynamic Operating Current (Both Ports Active)	$\overline{CE}_L \text{ and } \overline{CE}_R < V_{IH}, \text{ Outputs Open}$	—	—	65	120	—	65	100	mA
			I	—	65	175	—	65	135	
			X	—	65	180	—	65	150	
I_{SB1}	Standby Current (Both Ports Standby)	$\overline{CE}_L \text{ and } \overline{CE}_R > V_{IH}$	—	—	15	25	—	15	20	mA
			I	—	15	50	—	15	30	
			X	—	15	50	—	15	30	
I_{SB2}	Standby Current (One Port Standby)	$\overline{CE}_L \text{ or } \overline{CE}_R \geq V_{IH}, \text{ other } \overline{CE} < V_{IL}, \text{ Active Port Data Pins Open}$	—	—	40	100	—	40	60	mA
			I	—	40	110	—	40	75	
			X	—	40	110	—	40	75	
I_{SB3}	CMOS Standby Current (Both Ports Standby)	$\overline{CE}_L \text{ and } \overline{CE}_R > V_{DD} - 0.2V$ $V_{IN} \geq V_{DD} - 0.2V \text{ or } V_{IN} \leq V_{SS} + 0.2V$	—	—	5	10000	—	3	100	μA
			I	—	5	15000	—	3	250	
			X	—	5	15000	—	3	4000	
I_{SB4}	CMOS Standby Current (One Port Standby)	$\overline{CE}_L \text{ or } \overline{CE}_R \geq V_{DD} - 0.2V, \text{ Other } \overline{CE} \leq V_{IL}, V_{IN} \geq V_{DD} - 0.2V \text{ or } V_{IN} \leq V_{SS} + 0.2V, \text{ Active Data Pins Open}$	—	—	40	90	—	35	55	mA
			I	—	40	90	—	35	65	
			X	—	40	90	—	35	65	
V_{OL}	Output Low Voltage (I/O_0 - I/O_7)	$I_{OL} = 3.5 \text{ mA}$	—	—	—	0.4	—	—	0.4	V
		$I_{OL} = 8.0 \text{ mA}$	—	—	—	0.5	—	—	0.5	
V_{OL}	Open Drain Output Low Voltage (BUSY)	$I_{OL} = 8.0 \text{ mA}$	—	—	—	0.5	—	—	0.5	V
V_{OH}	Output High Voltage	$I_{OH} = -4.0 \text{ mA}$	—	—	—	—	—	—	—	V

NOTES:

- $V_{DD} = 5.0V, T_A = +25^\circ C$.
 - $V_{IL} \text{ (min)} = -3.5$ for pulse width less than 20 ns.
 * (—) $T_A = 0^\circ C \text{ to } 70^\circ C, V_{DD} = 5V \pm 10\%, V_{SS} = 0V$
 ** (I) $T_A = -40^\circ C \text{ to } +85^\circ C, V_{DD} = 5V \pm 10\%, V_{SS} = 0V$
 *** (X) $T_A = -55^\circ C \text{ to } +125^\circ C, V_{DD} = 5V \pm 10\%, V_{SS} = 0V$ unless otherwise noted
- For availability in a particular temperature range, refer to Device Usage Chart, Page 1.

AC Characteristics

For operating conditions, refer to Temperature Range Marking

Read Cycle

Symbol	Parameter	Range	55		70		90		120		Unit
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
t_{RC}	Read Cycle Time		55	—	70	—	90	—	120	—	ns
t_{AA}	Address Access Time		—	55	—	70	—	90	—	120	ns
t_{ACE}	Chip Enable Access Time		—	55	—	70	—	90	—	120	ns
t_{AOE}	Output Enable Access Time	* —	—	20	—	35	—	40	N/A	N/A	ns
		** I	N/A	N/A	—	35	—	40	—	40	
		*** X	N/A	N/A	—	35	—	40	—	40	
t_{OH}	Output Hold From Address Change	—	10	—	10	—	10	—	N/A	N/A	ns
		I	N/A	N/A	10	—	10	—	20	—	
		X	N/A	N/A	10	—	15	—	20	—	
t_{LZ}	Output Low-Z Time (1)	—	5	—	5	—	5	—	N/A	N/A	ns
		I	N/A	N/A	5	—	5	—	10	—	
		X	N/A	N/A	5	—	5	—	10	—	
t_{HZ}	Output High-Z Time (1)		—	20	—	35	—	40	—	40	ns
t_{PU}	$\overline{CE}$ to Power Up Time		0	—	0	—	0	—	0	—	ns
t_{PD}	Chip Disable to Power Down Time		—	35	—	40	—	50	—	50	ns

Write Cycle

Symbol	Parameter	Range	55		70		90		120		Unit
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
t_{WC}	Write Cycle Time		55	—	70	—	90	—	120	—	ns
t_{EW}	Chip Enable to End of Write		50	—	65	—	85	—	110	—	ns
t_{AW}	Address Valid to End of Write		50	—	65	—	85	—	110	—	ns
t_{AS}	Address Setup Time		0	—	0	—	0	—	0	—	ns
t_{WP}	Write Pulse Width	—	30	—	40	—	50	—	N/A	N/A	ns
		I	N/A	N/A	40	—	50	—	60	—	
		X	N/A	N/A	40	—	50	—	60	—	
t_{WR}	Write Recovery Time		5	—	5	—	5	—	5	—	ns
t_{DW}	Data Valid to End of Write	—	20	—	25	—	30	—	N/A	N/A	ns
		I	N/A	N/A	25	—	30	—	35	—	
		X	N/A	N/A	25	—	30	—	35	—	
t_{DH}	Data Hold Time		0	—	0	—	0	—	0	—	ns
t_{HZ}	Output High-Z Time (1)		—	20	—	35	—	40	—	50	ns
t_{WZ}	$\overline{WE}$ to Output High-Z (1)		0	25	0	35	0	40	0	50	ns
t_{OW}	Output Active From End of Write (1)		0	—	0	—	0	—	0	—	ns

NOTE:

1. Transition is measured ± 500 mV from low or high voltage with load (Figure 2). This parameter is sampled and not 100% tested.

* (—) $T_A = 0^\circ\text{C}$ to 70°C , $V_{DD} = 5V \pm 10\%$, $V_{SS} = 0V$

** (I) $T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$, $V_{DD} = 5V \pm 10\%$, $V_{SS} = 0V$

*** (X) $T_A = -55^\circ\text{C}$ to $+125^\circ\text{C}$, $V_{DD} = 5V \pm 10\%$, $V_{SS} = 0V$ unless otherwise noted

For part availability in a particular temperature range, refer to Device Usage Chart, Page 1.

AC Characteristics

BUS $\overline{\text{Y}}$ Timing ⁽¹⁾

Symbol	Parameter	55		70		90		120		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
t_{RC}	Read Cycle Time	55	—	70	—	90	—	120	—	ns
t_{WC}	Write Cycle Time	55	—	70	—	90	—	120	—	ns
t_{BAA}	$\overline{\text{BUSY}}$ Access Time to Address	—	40	—	45	—	45	—	60	ns
t_{BDA}	$\overline{\text{BUSY}}$ Disable Time to Address	—	45	—	45	—	45	—	60	ns
t_{BAC}	$\overline{\text{BUSY}}$ Access Time to $\overline{\text{CE}}$	—	40	—	45	—	45	—	60	ns
t_{BDC}	$\overline{\text{BUSY}}$ Disable Time to $\overline{\text{CE}}$	—	45	—	45	—	45	—	60	ns
t_{APS}	Arbitration Priority Setup Time	10	—	10	—	10	—	10	—	ns

NOTE:

- Commercial Temperature Range— $T_A = 0^\circ\text{C}$ to 70°C , $V_{DD} = 5V \pm 10\%$, $V_{SS} = 0V$
 Industrial Temperature Range— $T_A = 40^\circ\text{C}$ to $+85^\circ\text{C}$, $V_{DD} = 5V \pm 10\%$, $V_{SS} = 0V$
 Extended Temperature Range— $T_A = -55^\circ\text{C}$ to $+125^\circ\text{C}$, $V_{DD} = 5V \pm 10\%$, $V_{SS} = 0V$ unless otherwise noted.
 For availability in a particular temperature range, refer to Device Usage Chart, Page 1.

AC Test Conditions

Input Pulse Levels	V_{SS} to 3.0V
Input Rise and Fall Times	5 ns
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	See Figures 1, 2 and 3

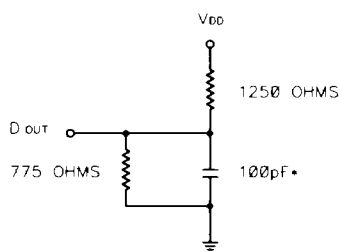


Figure 1.
*Including scope and jig.

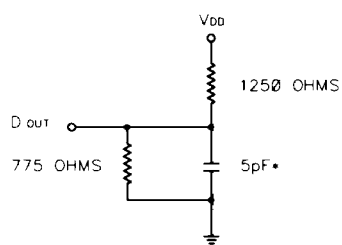


Figure 2.
(for t_{HZ} , t_{LZ} , t_{WZ} , and t_{OW})

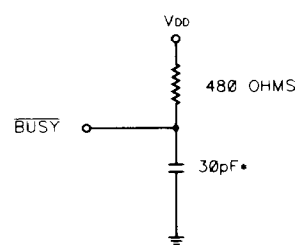
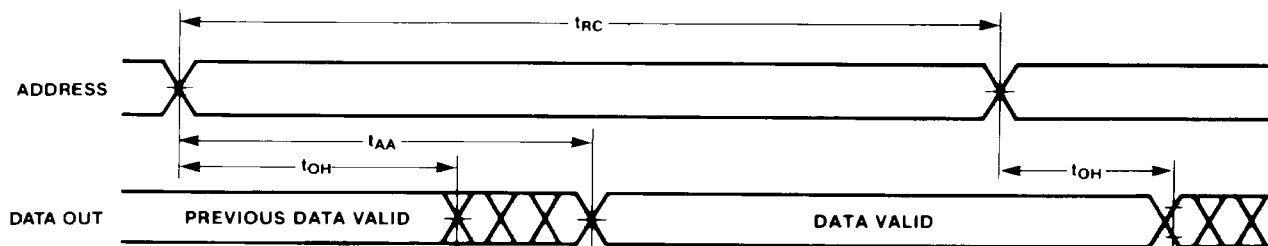
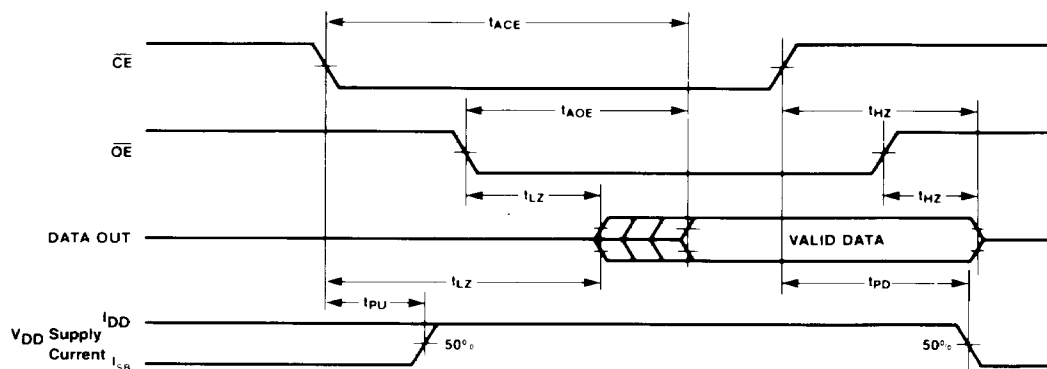
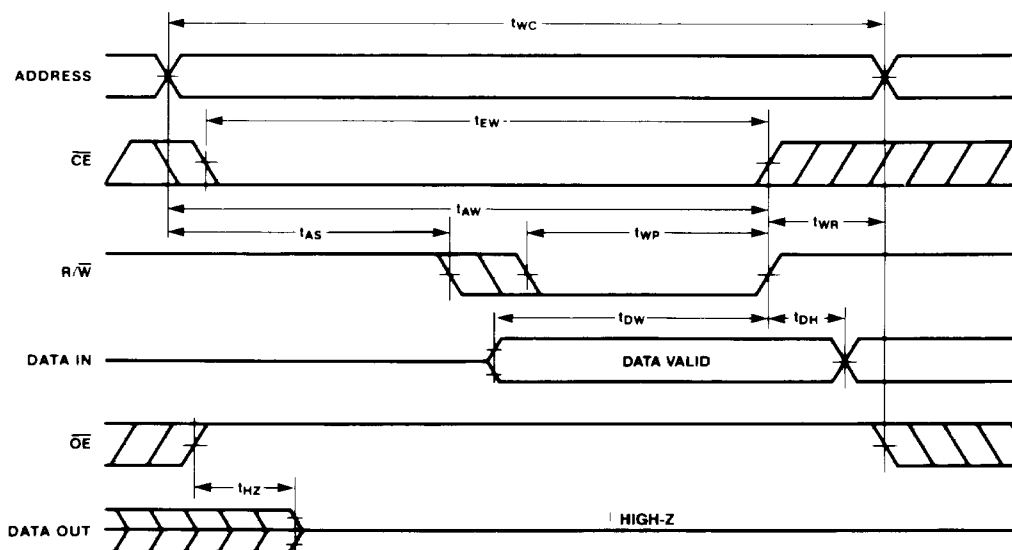


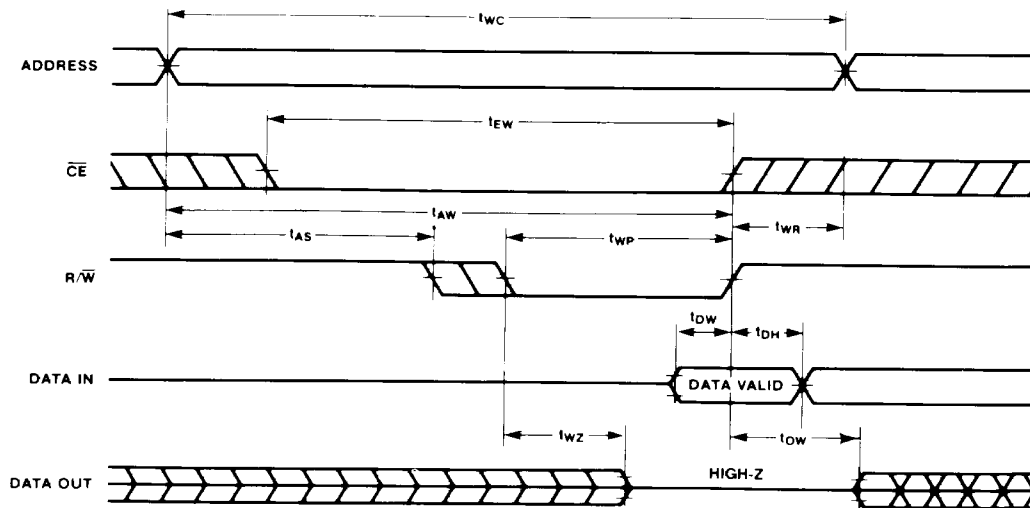
Figure 3.

Timing Waveform of Read Cycle No. 1 Either Side (1, 2, 6)



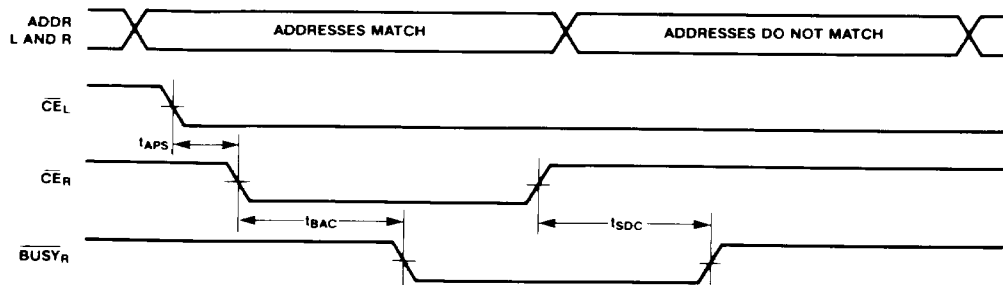
Timing Waveform of Read Cycle No. 2 Either Side (1, 3)

Timing Waveform of Write Cycle No. 2 Either Side (4, 7)


Timing Waveform of Write Cycle No. 1 Either Side (4, 7)

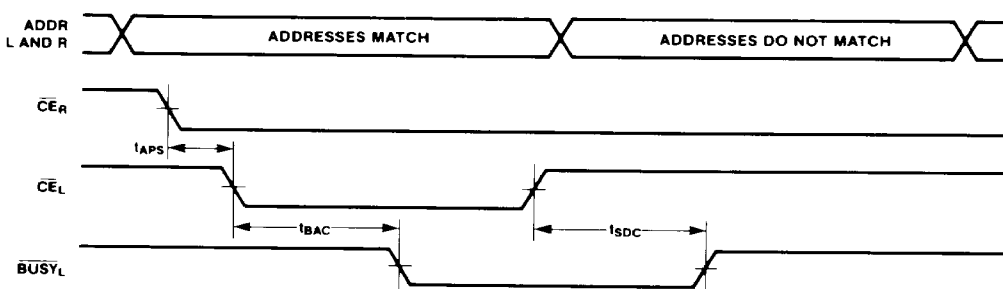


Timing Waveform of Contention Cycle No. 1 $\overline{CE}$ Arbitration

$\overline{CE}_L$ VALID FIRST:

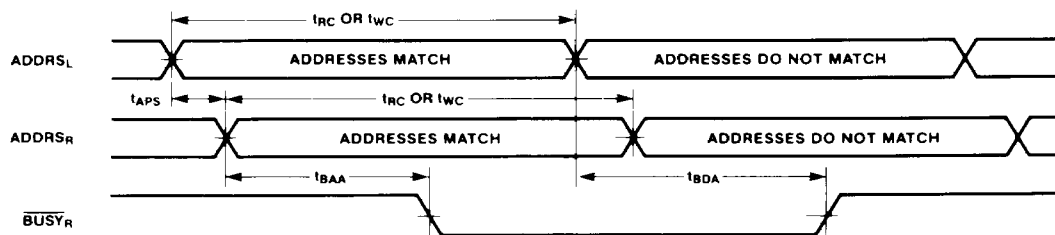


$\overline{CE}_R$ VALID FIRST:

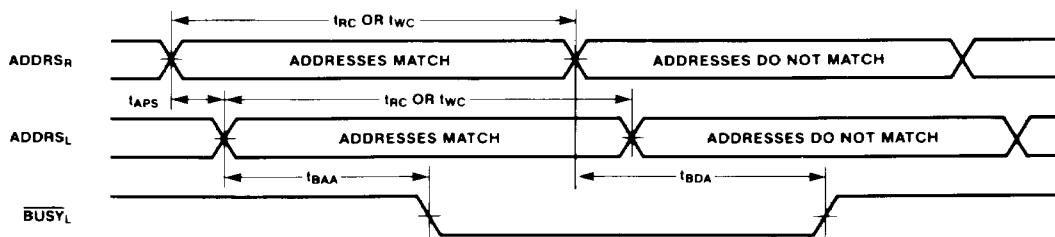


Timing Waveform of Contention Cycle No. 2 Address Valid Arbitration⁽⁵⁾

LEFT ADDRESS VALID FIRST



RIGHT ADDRESS VALID FIRST



NOTES:

1. $R/\overline{W}$ is high for Read Cycles.
2. Device is continuously enabled. $\overline{CE} = V_{IL}$.
3. Addresses valid prior to or coincident with $\overline{CE}$ transition low.
4. If $\overline{CE}$ goes high simultaneously with $R/\overline{W}$ high, the outputs remain in the high impedance state.
5. $\overline{CE}_L = \overline{CE}_R = V_{IL}$.
6. $\overline{OE} = V_{IL}$.
7. $R/\overline{W} = V_{IH}$ during address transition.

Data Retention Characteristics

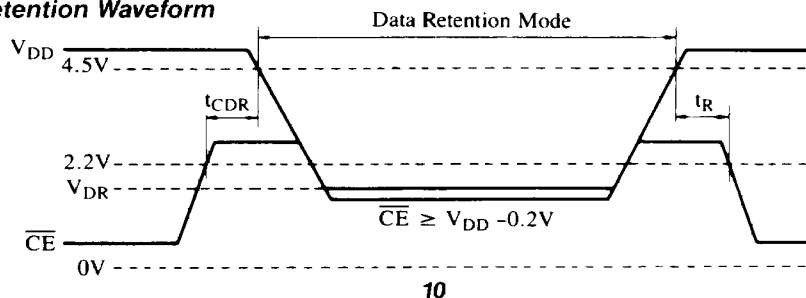
V61C32L

Symbol	Parameter	Test Conditions	Min.	Typ. (1)	Max.	Unit
V_{DR}	V_{DD} for Retention Data		2.0	—	—	V
I_{DDDR}	Data Retention Current	$V_{DD} = 3.0V, \overline{CE} \geq V_{DD} - 0.2V$ $V_{IN} \geq V_{DD} - 0.2V$ or $V_{IN} \leq +0.2V$	—	3	100 (3)	μA
t_{CDR}	Chip Deselect to Data Retention Time		0	—	—	ns
t_R	Operation Recovery Time		$t_{RC}^{(2)}$	—	—	ns

NOTES:

1. $V_{DD} = 2V, T_A = +25^\circ C$.
2. t_{RC} = Read Cycle Time.
3. 100 μA max. for $0^\circ C$ to $70^\circ C$. 250 μA max. for $-40^\circ C$ to $+85^\circ C$. 4000 μA max. for $-55^\circ C$ to $+125^\circ C$.

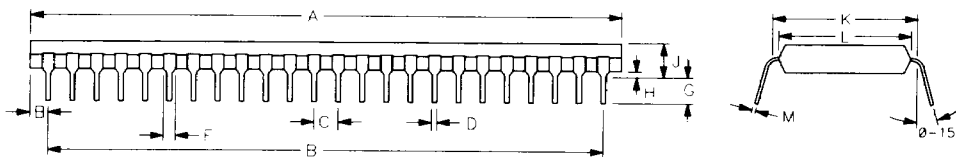
Low V_{DD} Data Retention Waveform



Package Outline

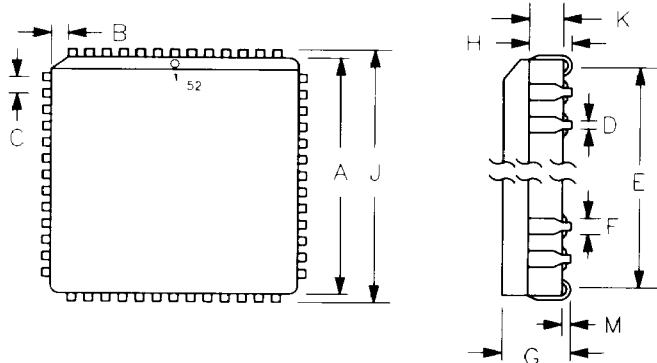
48 Pin Plastic

Dimension	Inches	Millimeters
A	2.460 max	62.484 max
B	.080	2.032
C	1	2.54
D	.015/ .020	.381/ .508
E	2.3	58.42
F	.040/ .065	1.016/ 1.651
G	.125/ .160	3.175/ 4.064
H	.015/ .065	.381/ 1.651
J	.160/ .225	4.064/ 5.715
K	.540/ .610	14.986/ 15.494
L	.530/ .550	13.462/ 13.970
M	.009/ .012	.229/ .305



52 Pin PLCC-J

Dimension	Inches	Millimeters
A	.760 max	19.30 max
B	.045	1.14
C	.050 typ	1.27 typ
D	.017 typ	.43 typ
E	.730 max	18.54 max
F	.026/ .032	.66/ .81
G	.180 max	4.57
H	.098 nom	2.49
J	.795	20.19
K	.055 nom	1.40
M	.030/ 0.45	.76/ 1.14



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